

## P-Channel Enhancement Mode Power MOSFET

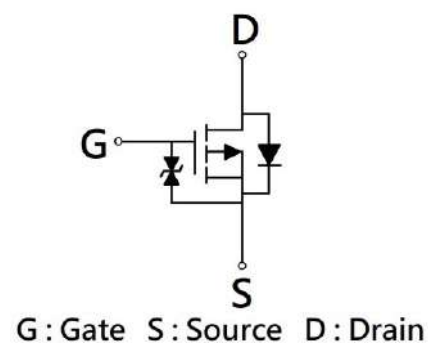
### Features :

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- ESD protected gate, typical >2kV (HBM)

SOT-23



|                                                 |              |
|-------------------------------------------------|--------------|
| $BV_{DSS}$                                      | -60V         |
| $I_D @ V_{GS} = -10V, T_A = 25^\circ C$         | -2.5A        |
| $R_{DS(ON)}$ typ. @ $V_{GS} = -10V, I_D = -2A$  | 65m $\Omega$ |
| $R_{DS(ON)}$ typ. @ $V_{GS} = -4.5V, I_D = -1A$ | 95m $\Omega$ |



### Ordering Information

| Device       | Package                                                   | Shipping               |
|--------------|-----------------------------------------------------------|------------------------|
| KNSB060P06KE | SOT-23<br>(Pb-free lead plating and halogen-free package) | 3000 pcs / Tape & Reel |

| Parameter                                                              |                      | Symbol                            | Limits   | Unit |
|------------------------------------------------------------------------|----------------------|-----------------------------------|----------|------|
| Drain-Source Voltage                                                   |                      | V <sub>DS</sub>                   | -60      | V    |
| Gate-Source Voltage                                                    |                      | V <sub>GS</sub>                   | ±20      |      |
| Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>A</sub> =25°C |                      | I <sub>D</sub>                    | -2.5     | A    |
| Continuous Drain Current @ V <sub>GS</sub> =-10V, T <sub>A</sub> =70°C |                      |                                   | -2       |      |
| Pulsed Drain Current                                                   |                      | I <sub>DM</sub>                   | -10      |      |
| Continuous Body Diode Forward Current @ T <sub>A</sub> =25°C           |                      | I <sub>S</sub>                    | -0.8     |      |
| Total Power Dissipation                                                | T <sub>A</sub> =25°C | P <sub>D</sub>                    | 0.9      | W    |
|                                                                        | T <sub>A</sub> =70°C |                                   | 0.6      |      |
| Operating Junction and Storage Temperature Range                       |                      | T <sub>J</sub> , T <sub>stg</sub> | -55~+150 | °C   |

## Thermal Data

| Parameter                               | Symbol          | Steady State | Unit          |
|-----------------------------------------|-----------------|--------------|---------------|
| Thermal Resistance, Junction-to-ambient | $R_{\theta JA}$ | 132          | $^{\circ}C/W$ |

Note:

- \*a. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR -4 board with 2 oz. copper, in a still air environment with  $T_A=25^{\circ}C$ . The power dissipation  $P_D$  is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^{\circ}C$ . The value in any given application depends on the user's specific board design.
- \*b. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}C$ . Ratings are based on low frequency and low duty cycles to keep initial  $T_J=25^{\circ}C$ .

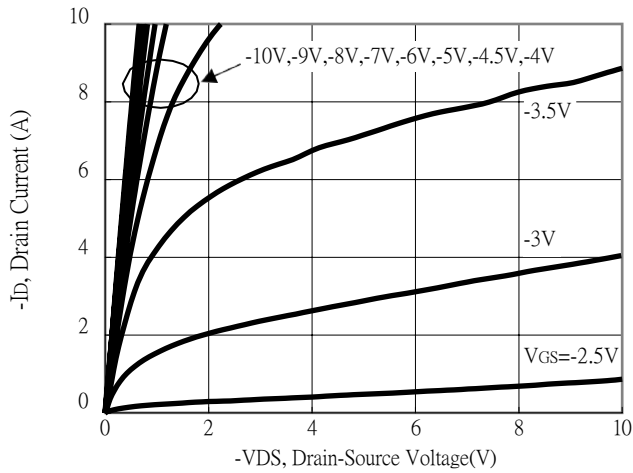
| Symbol                    | Min. | Typ. | Max. | Unit | Test Conditions                                                                        |
|---------------------------|------|------|------|------|----------------------------------------------------------------------------------------|
| Static                    |      |      |      |      |                                                                                        |
| BV <sub>DSS</sub>         | -60  | -    | -    | V    | V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA                                            |
| V <sub>GS(th)</sub>       | -1   | -    | -2.5 |      | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA                              |
| G <sub>FS</sub>           | -    | 5.4  | -    | S    | V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A                                             |
| I <sub>GSS</sub>          | -    | -    | ±10  | μA   | V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V                                             |
| I <sub>DSS</sub>          | -    | -    | -1   |      | V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V                                             |
| R <sub>DS(ON)</sub>       | -    | 65   | 85   | mΩ   | V <sub>GS</sub> =-10V, I <sub>D</sub> =-2A                                             |
|                           | -    | 95   | 135  |      | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A                                            |
| Dynamic                   |      |      |      |      |                                                                                        |
| C <sub>iss</sub>          | -    | 535  | -    | pF   | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1MHz                                     |
| C <sub>oss</sub>          | -    | 70   | -    |      |                                                                                        |
| C <sub>rss</sub>          | -    | 52   | -    |      |                                                                                        |
| R <sub>g</sub>            | -    | 5.7  | -    | Ω    | f=1MHz                                                                                 |
| Q <sub>g</sub> *1, 2      | -    | 6.2  | -    | nC   | V <sub>DS</sub> =-30V, I <sub>D</sub> =-2A, V <sub>GS</sub> =-4.5V                     |
| Q <sub>g</sub> *1, 2      | -    | 12   | -    |      | V <sub>DS</sub> =-30V, I <sub>D</sub> =-2A, V <sub>GS</sub> =-10V                      |
| Q <sub>gs</sub> *1, 2     | -    | 1.8  | -    |      |                                                                                        |
| Q <sub>gd</sub> *1, 2     | -    | 2.7  | -    |      |                                                                                        |
| t <sub>d(ON)</sub> *1, 2  | -    | 6.4  | -    | ns   | V <sub>DS</sub> =-30V, I <sub>D</sub> =-2A, V <sub>GS</sub> =-10V, R <sub>GS</sub> =1Ω |
| t <sub>r</sub> *1, 2      | -    | 18   | -    |      |                                                                                        |
| t <sub>d(OFF)</sub> *1, 2 | -    | 29   | -    |      |                                                                                        |
| t <sub>f</sub> *1, 2      | -    | 13   | -    |      |                                                                                        |
| Source-Drain Diode        |      |      |      |      |                                                                                        |
| V <sub>SD</sub> *1        | -    | -0.8 | -1.2 | V    | I <sub>S</sub> =-2A, V <sub>GS</sub> =0V                                               |
| t <sub>rr</sub>           | -    | 10   | -    | ns   | I <sub>F</sub> =-2A, dI <sub>F</sub> /dt=100A/μs                                       |
| Q <sub>rr</sub>           | -    | 5.5  | -    | μC   |                                                                                        |

Note:

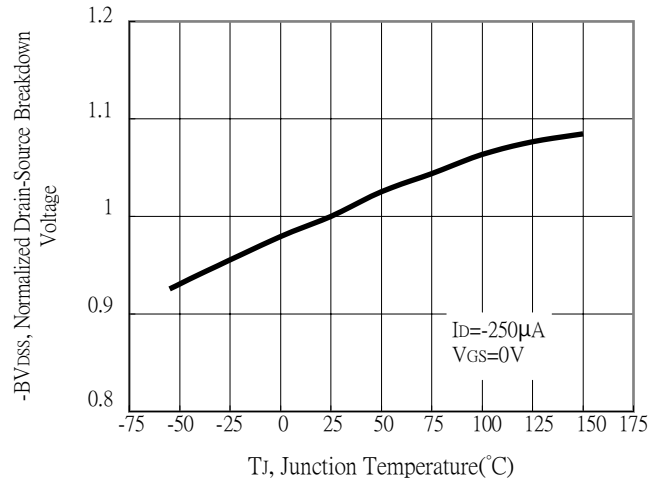
\*1. Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$

\*2. Independent of operating temperature

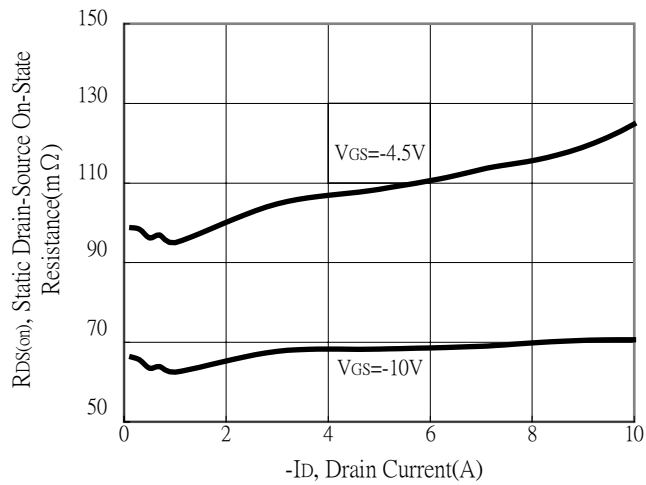
Typical Output Characteristics



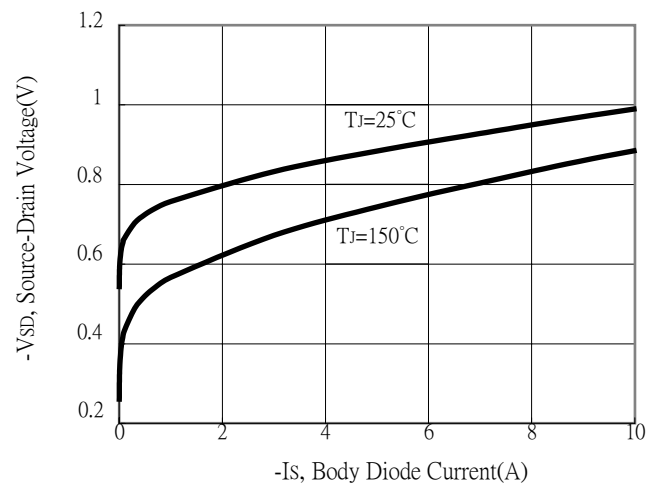
Breakdown Voltage vs Junction Temperature



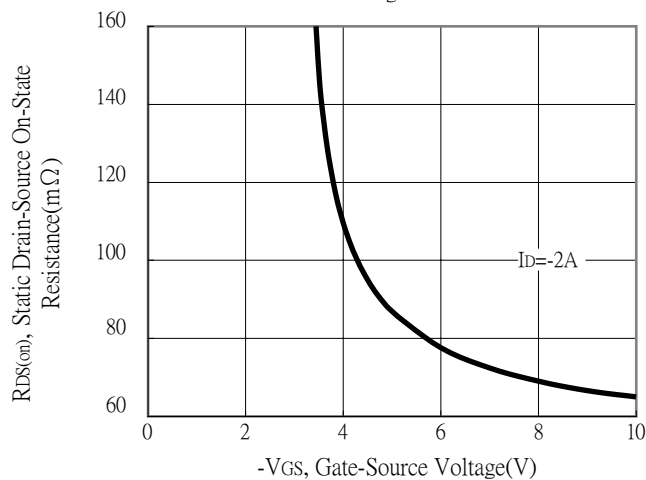
Static Drain-Source On-State resistance vs Drain Current



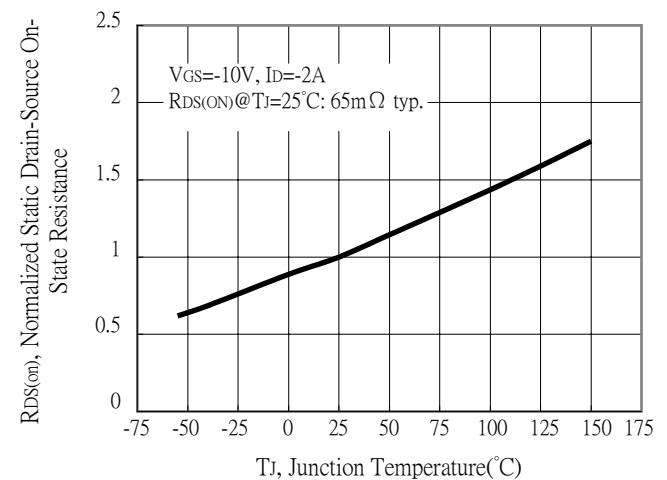
Body Diode Current vs Source-Drain Voltage



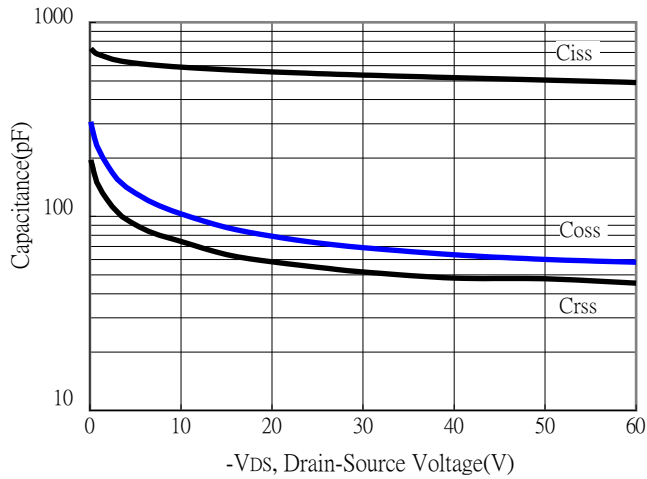
Static Drain-Source On-State Resistance vs Gate-Source Voltage



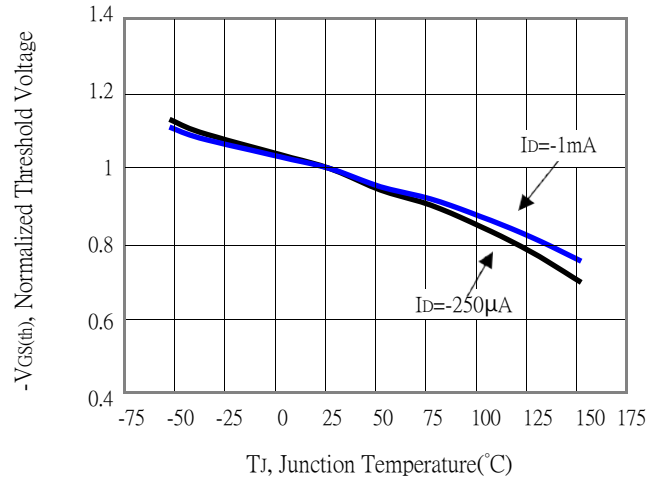
Drain-Source On-State Resistance vs Junction Temperature



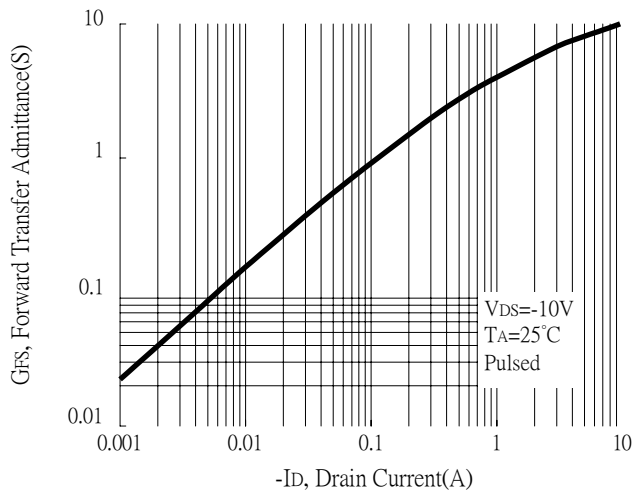
Capacitance vs Drain-to-Source Voltage



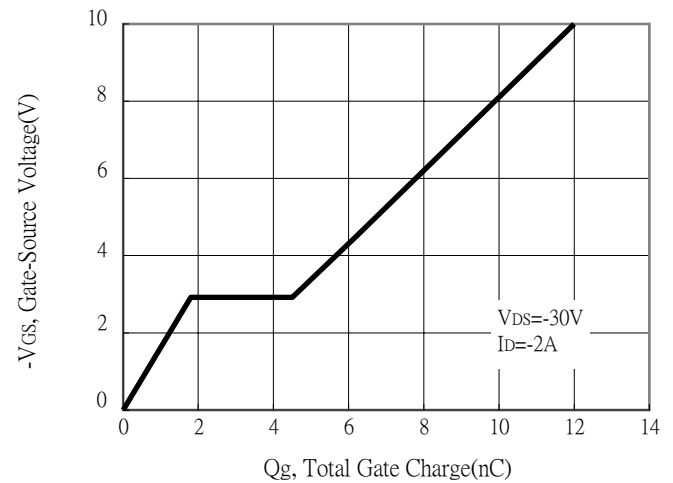
Threshold Voltage vs Junction Temperature



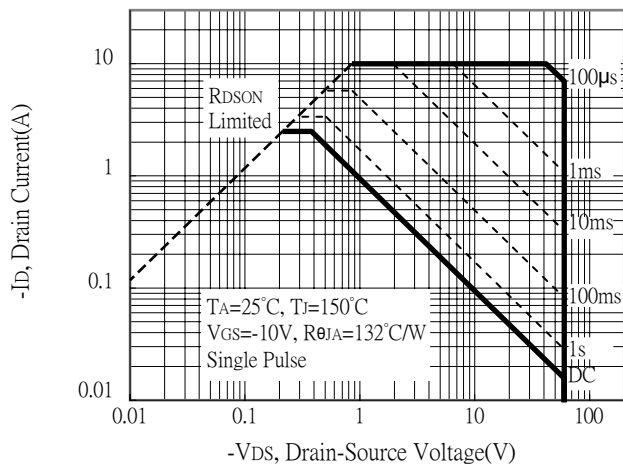
Forward Transfer Admittance vs Drain Current



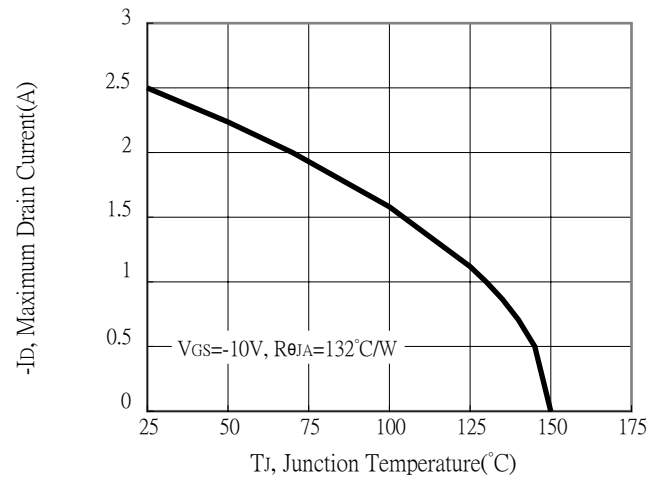
Gate Charge Characteristics



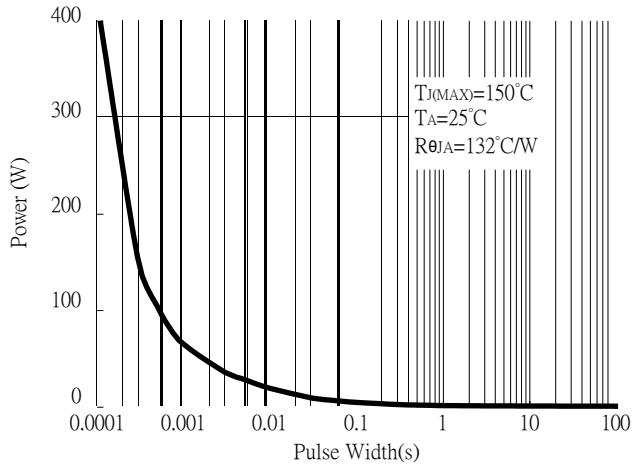
Maximum Safe Operating Area



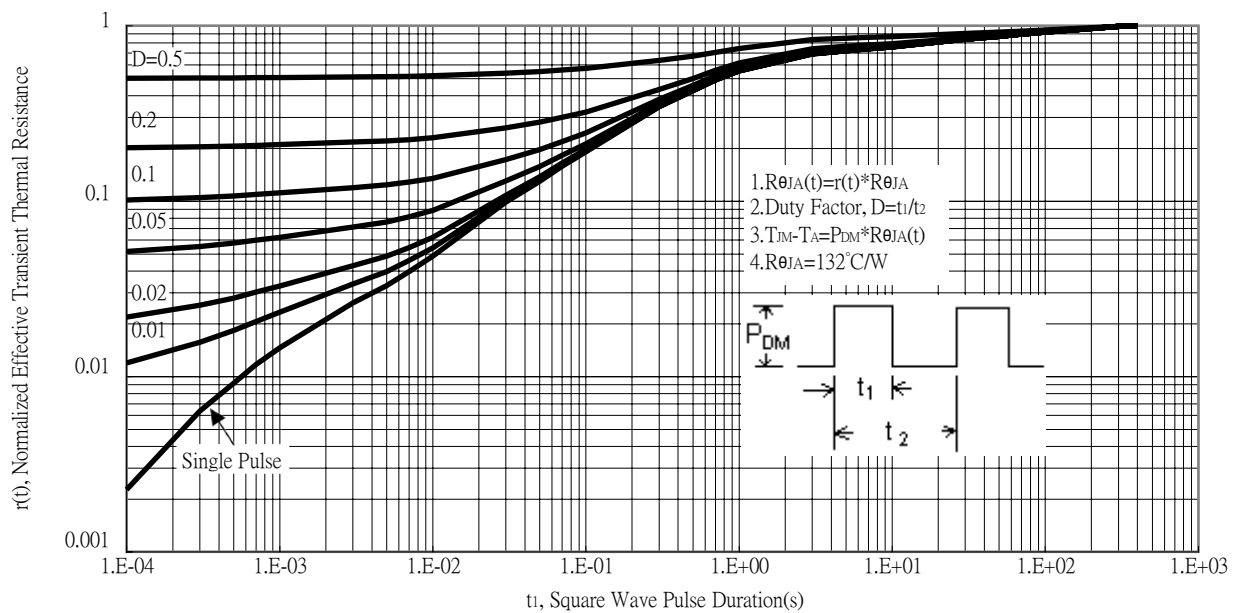
Maximum Drain Current vs Junction Temperature



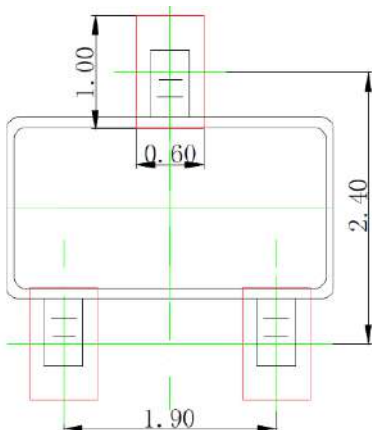
Single Pulse Power Rating, Junction to Ambient



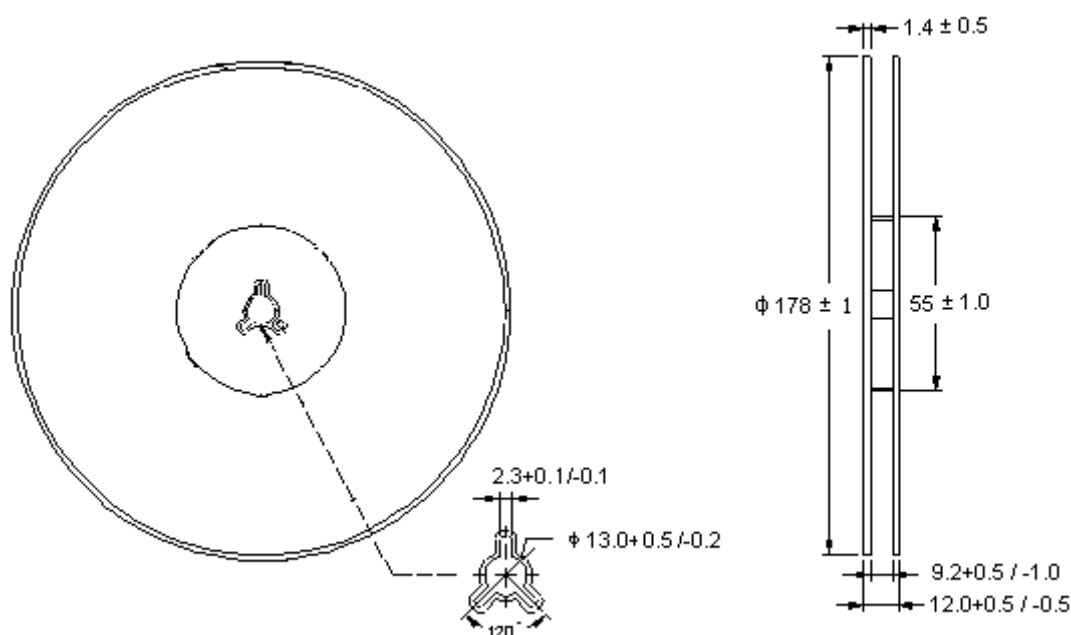
Transient Thermal Response Curves



## Recommended soldering footprint

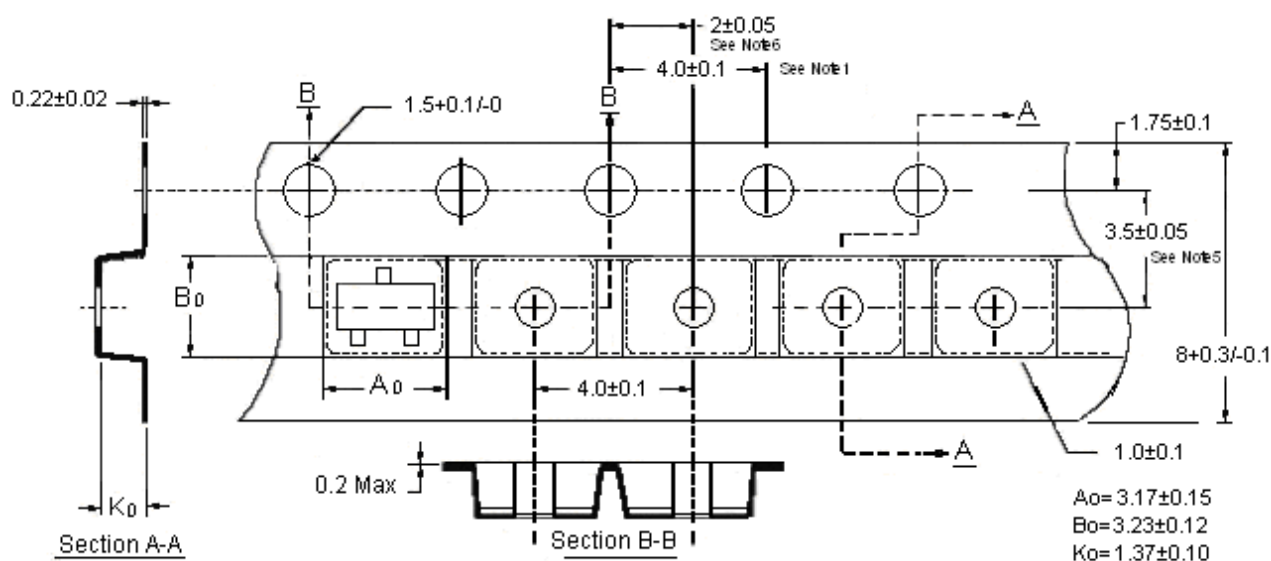


Unit : mm



Unit: millimeter

## Carrier Tape Dimension

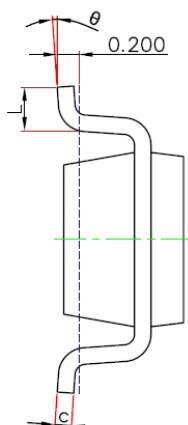
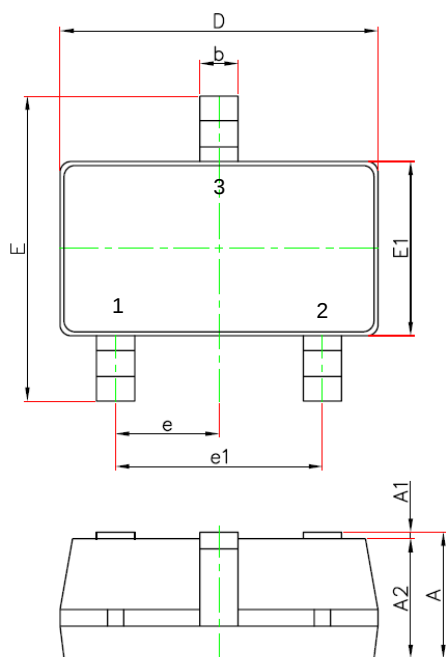


### Notes:

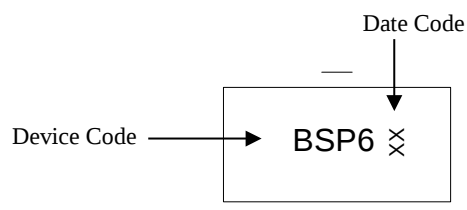
1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material : conductive Black Polystyrene.
4.  $A_0$  &  $B_0$  measured on a plane 0.3mm above the bottom of the pocket.
5.  $K_0$  measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

## SOT-23 Dimension



Marking:



Style: Pin 1.Gate 2.Source 3.Drain

Date Code: Year+Month  
 Year: 3→2003, 4→2004  
 Month: 1→1, 2→2, . . .  
 9→9, A→10, B→11, C→12

3-Lead SOT-23 Plastic  
 Surface Mounted Package

| DIM | Inches |       | Millimeters |      | DIM | Inches    |       | Millimeters |      |
|-----|--------|-------|-------------|------|-----|-----------|-------|-------------|------|
|     | Min.   | Max.  | Min.        | Max. |     | Min.      | Max.  | Min.        | Max. |
| A   | 0.041  | 0.049 | 1.05        | 1.25 | E1  | 0.059     | 0.067 | 1.50        | 1.70 |
| A1  | 0.000  | 0.004 | 0.00        | 0.10 | E   | 0.104     | 0.116 | 2.65        | 2.95 |
| A2  | 0.041  | 0.045 | 1.05        | 1.15 | e   | 0.037 BSC |       | 0.95 BSC    |      |
| b   | 0.012  | 0.020 | 0.30        | 0.50 | e1  | 0.071     | 0.079 | 1.80        | 2.00 |
| c   | 0.004  | 0.008 | 0.10        | 0.20 | L   | 0.012     | 0.024 | 0.30        | 0.60 |
| D   | 0.111  | 0.119 | 2.82        | 3.02 | θ   | 0°        | 8°    | 0°          | 8°   |